

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	13146	((438/149) or (438/151) or (438/164) or (438/166) or (438/311) or (438/412) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/489) or (438/490) or (438/595) or (438/596) or (438/704) or (438/706) or (438/735) or (438/745) or (438/764) or (438/795) or (438/800) or (438/902)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/30 16:01
L2	8	1 and ((silicon near2 spacer\$1) near5 ((active adj(region\$1 or layer\$1)) or channel\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/30 16:01
S1	10057	((438/149) or (438/151) or (438/164) or (438/166) or (438/311) or (438/412) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/489) or (438/490) or (438/595) or (438/596) or (438/704) or (438/406) or (438/735) or (438/745) or (438/764) or (438/795) or (438/800) or (438/902)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/30 16:01
S2	12	("4330363") or ("4592799") or ("5021119") or ("5395481") or ("6495405")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/08 23:06
S3	2901	((polycrystalline near2 silicon) or (poly adj silicon)) near2 (tft or ((thin near2 film) near2 transistor\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:34
S4	1053	((polycrystalline near2 silicon) or (poly adj silicon)) near3 (spacer\$1 or sidewall\$1 or (sidewall near2 spacer\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 21:19

S5	8	S3 and S4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:36
S6	1	S1 and S5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:36
S7	1152	((polycrystalline near2 silicon) or (poly adj silicon)) near3 (spacer\$1 or sidewall\$1 or capp\$3 or (capp\$3 near2 (layer or film)) or (sidewall near2 spacer\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 18:04
S8	4082	S7 and3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:39
S9	12	S7 and S3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:39
S10	1	S9 and S1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:39
S11	11	S9 not S10	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:40
S12	16	((polycrystalline near2 silicon) or (poly adj silicon)) near3 (spacer\$1 or sidewall\$1 or (sidewall near2 spacer\$1)) same (active near2 (layer\$1 or film\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:44

S13	16	((polycrystalline near2 silicon) or (poly adj silicon)) near3 (spacer\$1 or sidewall\$1 or capp\$3 or (capp\$3 near2 (layer or film)) or (sidewall near2 spacer\$1)) same (active near2 (layer\$1 or film\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:54
S14	6	((polycrystalline near2 silicon) or (poly adj silicon)) near3 (spacer\$1 or sidewall\$1 or capp\$3 or (capp\$3 near2 (layer or film)) or (sidewall near2 spacer\$1)) near10 (active near2 (layer\$1 or film\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:52
S15	10	S13 not S14	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:52
S16	0	("2004/0026738").URPN.	USPAT	OR	OFF	2004/12/08 17:53
S17	123	((polycrystalline near2 silicon) or (poly adj silicon)) near3 (spacer\$1 or sidewall\$1 or capp\$3 or (capp\$3 near2 (layer or film)) or (sidewall near2 spacer\$1))and (active near2 (layer\$1 or film\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:55
S18	107	S17 not S13	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:55
S19	33	((polycrystalline near2 silicon) or (poly adj silicon)) near3 (spacer\$1 or sidewall\$1 or capp\$3 or (capp\$3 near2 (layer or film)) or (sidewall near2 spacer\$1)) same (crystall\$7 or recrystall\$7)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 18:05
S20	7	S19 and (active near2 (layer\$1 or film\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 18:07
S21	0	S19 not S7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 18:08

S22	26	S19 not S20	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 18:09
S23	106	((LTPS adj TFT) or (low adj temperature adj polycrystalline adj silicon adj thin adj film adj transistor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 21:21
S24	10057	((438/149) or (438/151) or (438/164) or (438/166) or (438/311) or (438/412) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/489) or (438/490) or (438/595) or (438/596) or (438/704) or (438/406) or (438/735) or (438/745) or (438/764) or (438/795) or (438/800) or (438/902)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/08 21:21
S25	103	S23 and "1"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 21:26
S26	21	S23 and S24	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 21:22
S27	75	S23 and (amorphous)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 22:30
S28	19	S27 and S24	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 21:26

S29	42860	(spc or (solid adj phas adj crystallization)) or (milc or (metal adj induced adj lateral adj crystallization)) or (ela or (excimer adj laser adj annealing))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 22:33
S30	27	S29 and S23	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 22:33
S31	0	("2004/0217424").URPN.	USPAT	OR	OFF	2004/12/08 22:38
S32	1	("6242292").PN.	USPAT	OR	OFF	2004/12/08 22:38
S33	52	( "3848104"   "4046618"   "4059461"   "4083272"   "4160263"   "4234358"   "4249960"   "4266986"   "4309225"   "4328553"   "4341569"   "4370175"   "4439245"   "4463028"   "4468551"   "4469551"   "4545823"   "4734550"   "4764485"   "4803528"   "4835704"   "4862227"   "4937618"   "4942058"   "4956539"   "4970366"   "5217921"   "5219786"   "5221365"   "5247375"   "5313076"   "5352291"   "5365875"   "5372836"   "5413958"   "5424230"   "5424244"   "5432122"   "5477073"   "5561081"   "5572046"   "5578520"   "5589406"   "5612251"   "5622814"   "5648277"   "5696003"   "5708252"   "5712191"   "5736414"   "5756364"   "5858473").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/12/08 22:40
S34	20	((("5365080") or ("5847419") or ("6607948") or ("6674100") or ("5063166") or ("4962051") or ("4962051") or ("4914053") or ("4868614"))).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/08 23:10
S35	2	("5818053").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/08 23:10

S36	10741	((438/149) or (438/151) or (438/164) or (438/166) or (438/311) or (438/412) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/489) or (438/490) or (438/595) or (438/596) or (438/704) or (438/406) or (438/735) or (438/745) or (438/764) or (438/795) or (438/800) or (438/902)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/13 15:38
S37	121	S36 and ((polysilicon near spacer\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:13
S38	0	S36 and ((polysilicon near spacer\$1) near (active adj (layer\$1 or film\$1)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:53
S39	1	S36 and ((polysilicon near spacer\$1) same (active adj (layer\$1 or film\$1)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:57
S40	0	((polysilicon near spacer\$1) near (active adj (layer\$1 or film\$1)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:53
S41	4	((polysilicon near spacer\$1) same (active adj (layer\$1 or film\$1)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:55
S42	16	((polysilicon near spacer\$1) and (active adj (layer\$1 or film\$1)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:55

S43	0	S36 and ((polysilicon near sidewall near spacer\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:57
S44	33	S36 and ((polysilicon near sidewall near spacer\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:04
S45	1	S44 and (active adj (layer\$1 or film\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:58
S46	10473	(polysilicon near\$3 spacer\$1) same (active near2 (layer\$1 or film\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:06
S47	2040	(polysilicon near\$3 spacer\$1) near (active near2 (layer\$1 or film\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:06
S48	0	(polysilicon near spacer\$1) near (active near2 (layer\$1 or film\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:06
S49	34	(polysilicon near spacer\$1) same (active near2 (layer\$1 or film\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:10
S50	153	(polysilicon near spacer\$1) and (active near2 (layer\$1 or film\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:10
S51	1	("5589406").PN.	USPAT	OR	OFF	2005/05/13 16:31

S52	395	( (ltps adj tft) or ((low near temperature) near transistor\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:34
S53	3	S52 and (polysilicon near2 spacer\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:36
S54	46	S52 and (active near (layer\$1 or film\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:41
S55	5	S54 and spacer\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:38
S56	5	S54 and ((spacer\$1 or sidewall) same (active near (layer\$1 or film\$1)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:39
S57	1	(soi near mosfet) same (polysilicon near spacer\$1) same (active near2 (layer\$1 or film\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:42
S58	4	(soi near mosfet) same ( spacer\$1 same (active near2 (layer\$1 or film\$1)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:44
S59	64	(soi near mosfet) same spacer\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:44
S60	36	"5589406"	USPAT	OR	OFF	2005/05/16 17:06
S61	1	("5589406").PN.	USPAT	OR	OFF	2005/05/16 17:06



S62	11786	((438/149) or (438/151) or (438/164) or (438/166) or (438/311) or (438/412) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/489) or (438/490) or (438/595) or (438/596) or (438/704) or (438/406) or (438/735) or (438/745) or (438/764) or (438/795) or (438/800) or (438/902)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/30 15:44
S63	0	("1and((siliconnear2spacer\$1)near5((activeadj(region\$1orlayer\$1))orchannel\$1))").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/30 15:45
S64	8	S62 and ((silicon near2 spacer\$1) near5 ((active adj(region\$1 or layer\$1)) or channel\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/30 16:01
S65	1318	(438/151).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/30 15:48
S66	571	(438/487).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/30 15:49
S67	1081	(438/166).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/30 15:49
S68	977	(438/795).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/30 15:49

S69	90	((silicon near2 spacer\$1) near5 ((active adj(region\$1 or layer\$1)) or channel\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/30 15:51
S70	6	S69 and (crystalliz\$5 or recrystalliz\$5)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/30 15:52